

IRF7241TR Datasheet



DiGi Electronics Part Number	IRF7241TR-DG
Manufacturer	Infineon Technologies
Manufacturer Product Number	IRF7241TR
Description	MOSFET P-CH 40V 6.2A 850
Detailed Description	P-Channel 40 V 6.2A (Ta) 2.5W (Ta) Surface Mount 8-SO

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Purchase and inquiry

Manufacturer Product Number:

IRF7241TR

Series:

HEXFET®

FET Type:

P-Channel

Drain to Source Voltage (Vdss):

40 V

Drive Voltage (Max Rds On, Min Rds On):

4.5V, 10V

Vgs(th) (Max) @ Id:

3V @ 250µA

Vgs (Max):

±20V

FET Feature:

-

Operating Temperature:

-55°C ~ 150°C (Tj)

Supplier Device Package:

8-SO

Manufacturer:

Infineon Technologies

Product Status:

Obsolete

Technology:

MOSFET (Metal Oxide)

Current - Continuous Drain (Id) @ 25°C:

6.2A (Ta)

Rds On (Max) @ Id, Vgs:

41mOhm @ 6.2A, 10V

Gate Charge (Qg) (Max) @ Vgs:

80 nC @ 10 V

Input Capacitance (Ciss) (Max) @ Vds:

3220 pF @ 25 V

Power Dissipation (Max):

2.5W (Ta)

Mounting Type:

Surface Mount

Package / Case:

8-SOIC (0.154", 3.90mm Width)

Environmental & Export classification

RoHS Status:

RoHS non-compliant

REACH Status:

REACH Unaffected

HTSUS:

8541.29.0095

Moisture Sensitivity Level (MSL):

1 (Unlimited)

ECCN:

EAR99

International
IR Rectifier

PD - 95294

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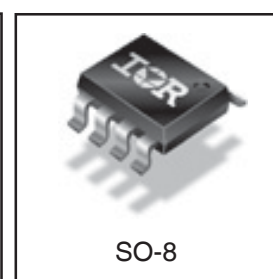
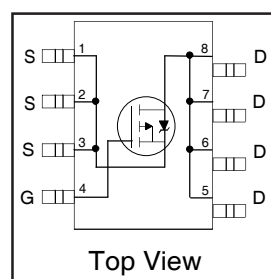
HEXFET® Power MOSFET

- Trench Technology
- Ultra Low On-Resistance
- P-Channel MOSFET
- Available in Tape & Reel
- Lead-Free

V_{DSS}	$R_{DS(on)}$ max (m Ω)	I_D
-40V	41 @ $V_{GS} = -10V$	-6.2A
	70 @ $V_{GS} = -4.5V$	-5.0A

Description

New trench HEXFET® Power MOSFETs from International Rectifier utilize advanced processing techniques to achieve extremely low on-resistance per silicon area. This benefit, combined with the ruggedized device design that HEXFET power MOSFETs are well known for, provides the designer with an extremely efficient and reliable device for use in battery and load management applications.



Absolute Maximum Ratings

	Parameter	Max.	Units
V_{DS}	Drain- Source Voltage	-40	V
$I_D @ T_A = 25^\circ C$	Continuous Drain Current, $V_{GS} @ -10V$	-6.2	A
$I_D @ T_A = 70^\circ C$	Continuous Drain Current, $V_{GS} @ -10V$	-4.9	
I_{DM}	Pulsed Drain Current ①	-25	
$P_D @ T_A = 25^\circ C$	Power Dissipation ③	2.5	W
$P_D @ T_A = 70^\circ C$	Power Dissipation ③	1.6	
	Linear Derating Factor	20	mW/ $^\circ C$
V_{GS}	Gate-to-Source Voltage	± 20	V
T_J, T_{STG}	Junction and Storage Temperature Range	-55 to + 150	$^\circ C$

Thermal Resistance

Symbol	Parameter	Typ.	Max.	Units
$R_{\theta JL}$	Junction-to-Drain Lead	—	20	$^\circ C/W$
$R_{\theta JA}$	Junction-to-Ambient ③	—	50	

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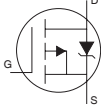
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International
IR Rectifier

Electrical Characteristics @ $T_J = 25^\circ\text{C}$ (unless otherwise specified)

	Parameter	Min.	Typ.	Max.	Units	Conditions
$V_{(BR)DSS}$	Drain-to-Source Breakdown Voltage	-40	—	—	V	$V_{GS} = 0V, I_D = -250\mu A$
$\Delta V_{(BR)DSS}/\Delta T_J$	Breakdown Voltage Temp. Coefficient	—	0.03	—	V/ $^\circ\text{C}$	Reference to 25°C , $I_D = -1\text{mA}$
$R_{DS(on)}$	Static Drain-to-Source On-Resistance	—	25	41	m Ω	$V_{GS} = -10V, I_D = -6.2A$ ②
		—	45	70		$V_{GS} = -4.5V, I_D = -5.0A$ ②
$V_{GS(th)}$	Gate Threshold Voltage	-1.0	—	-3.0	V	$V_{DS} = V_{GS}, I_D = -250\mu A$
g_{fs}	Forward Transconductance	8.9	—	—	S	$V_{DS} = -10V, I_D = -6.2A$
I_{DSS}	Drain-to-Source Leakage Current	—	—	-10	μA	$V_{DS} = -32V, V_{GS} = 0V$
		—	—	-25		$V_{DS} = -32V, V_{GS} = 0V, T_J = 70^\circ\text{C}$
I_{GSS}	Gate-to-Source Forward Leakage	—	—	-100	nA	$V_{GS} = -20V$
	Gate-to-Source Reverse Leakage	—	—	100		$V_{GS} = 20V$
Q_g	Total Gate Charge	—	53	80	nC	$I_D = -6.2A$
Q_{gs}	Gate-to-Source Charge	—	14	21		$V_{DS} = -32V$
Q_{gd}	Gate-to-Drain ("Miller") Charge	—	3.9	5.9		$V_{GS} = -10V$
$t_{d(on)}$	Turn-On Delay Time	—	24	—	ns	$V_{DD} = -20V$ ②
t_r	Rise Time	—	280	—		$I_D = -1.0A$
$t_{d(off)}$	Turn-Off Delay Time	—	210	—		$R_G = 6.0\Omega$
t_f	Fall Time	—	100	—		$V_{GS} = -10V$
C_{iss}	Input Capacitance	—	3220	—	pF	$V_{GS} = 0V$
C_{oss}	Output Capacitance	—	160	—		$V_{DS} = -25V$
C_{rss}	Reverse Transfer Capacitance	—	190	—		$f = 1.0\text{kHz}$

Source-Drain Ratings and Characteristics

	Parameter	Min.	Typ.	Max.	Units	Conditions
I_S	Continuous Source Current (Body Diode)	—	—	-2.5	A	MOSFET symbol showing the integral reverse p-n junction diode. 
I_{SM}	Pulsed Source Current (Body Diode) ①	—	—	-25		
V_{SD}	Diode Forward Voltage	—	—	-1.2	V	$T_J = 25^\circ\text{C}, I_S = -2.5A, V_{GS} = 0V$ ②
t_{rr}	Reverse Recovery Time	—	32	48	ns	$T_J = 25^\circ\text{C}, I_F = -2.5A$
Q_{rr}	Reverse Recovery Charge	—	45	68	nC	$di/dt = -100A/\mu s$ ②

Notes:

- ① Repetitive rating; pulse width limited by max. junction temperature.
- ② Pulse width $\leq 400\mu s$; duty cycle $\leq 2\%$.
- ③ Surface mounted on 1 in square Cu board

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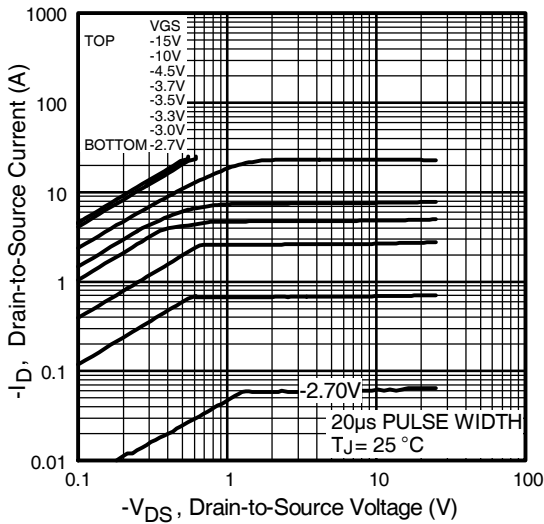


Fig 1. Typical Output Characteristics

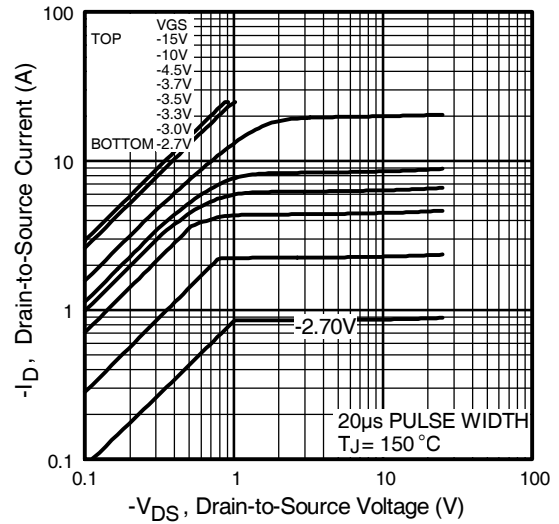


Fig 2. Typical Output Characteristics

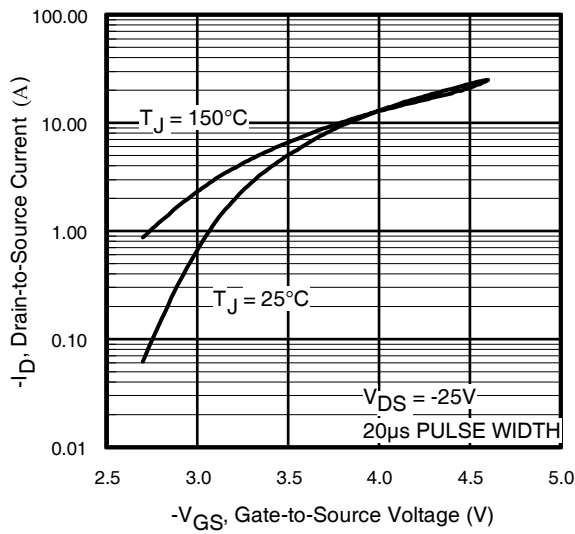


Fig 3. Typical Transfer Characteristics

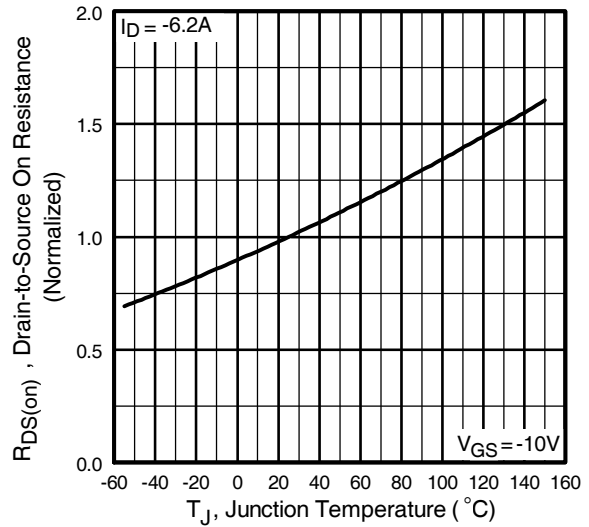


Fig 4. Normalized On-Resistance Vs. Temperature

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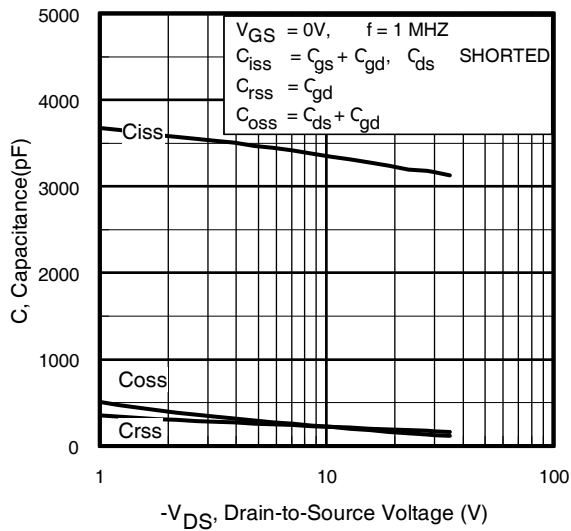


Fig 5. Typical Capacitance Vs. Drain-to-Source Voltage

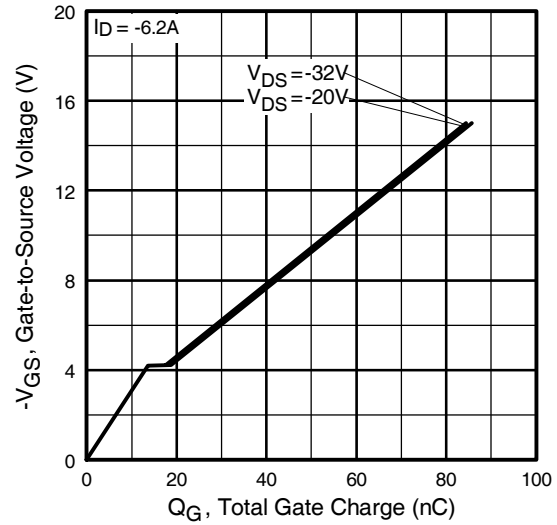


Fig 6. Typical Gate Charge Vs. Gate-to-Source Voltage

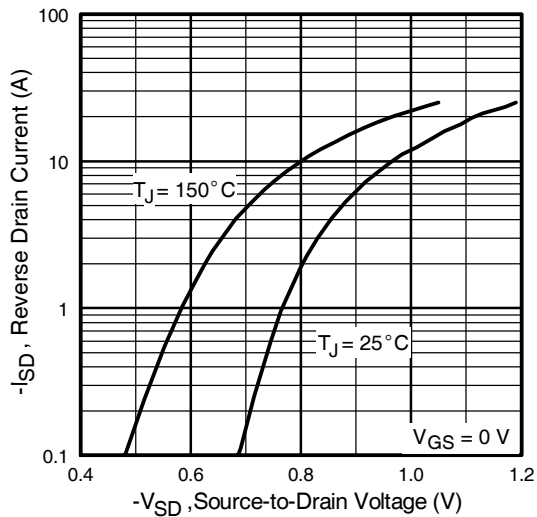


Fig 7. Typical Source-Drain Diode Forward Voltage

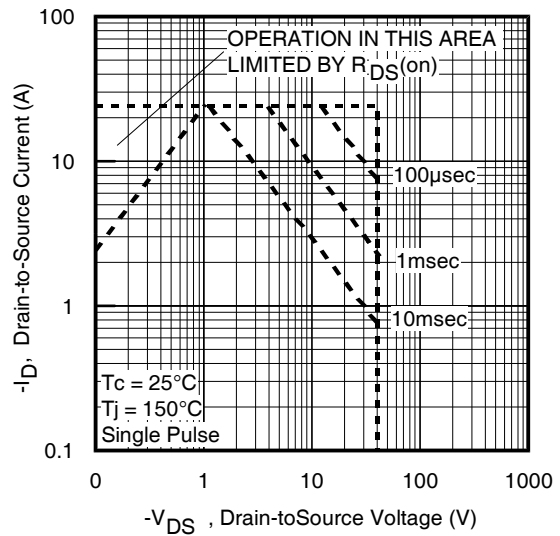


Fig 8. Maximum Safe Operating Area

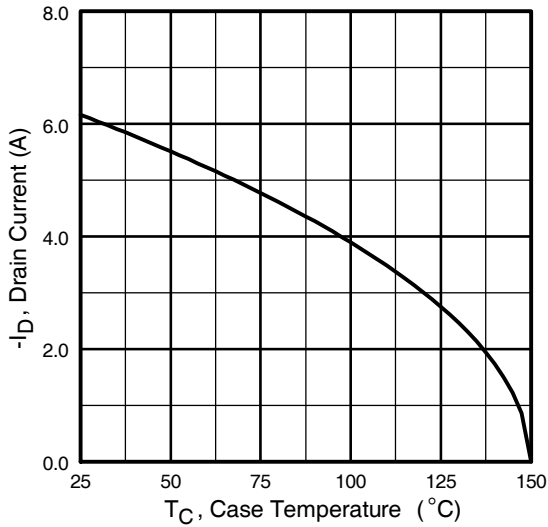


Fig 9. Maximum Drain Current Vs. Case Temperature

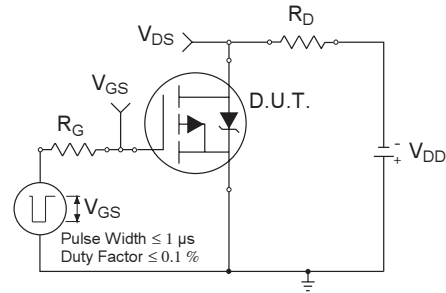


Fig 10a. Switching Time Test Circuit

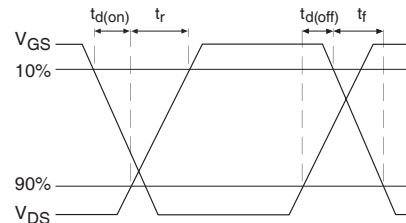


Fig 10b. Switching Time Waveforms

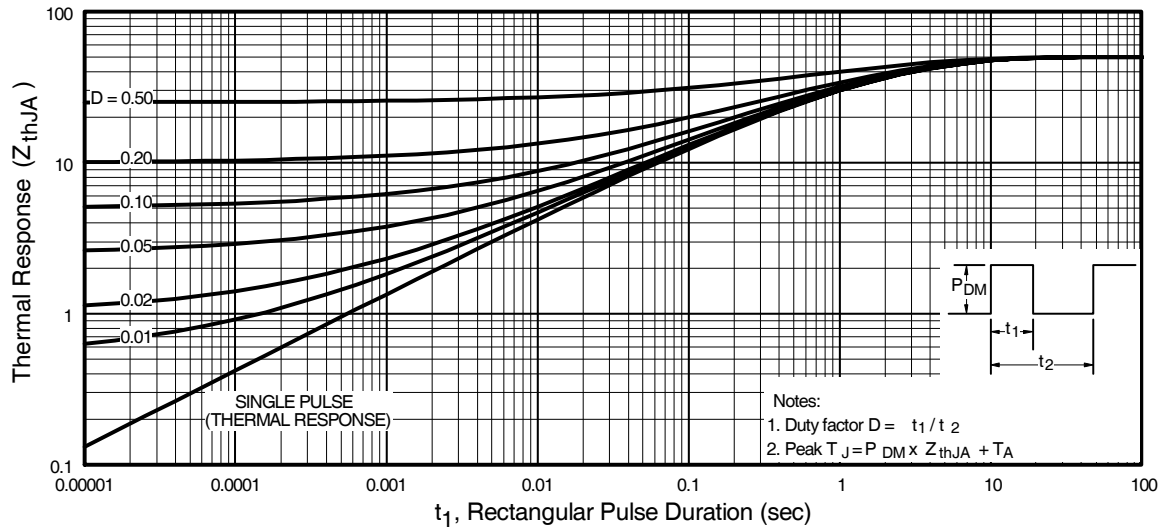


Fig 11. Maximum Effective Transient Thermal Impedance, Junction-to-Ambient

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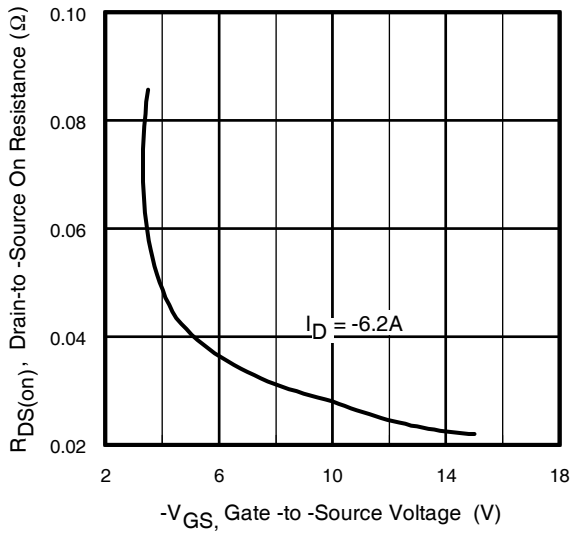


Fig 12. Typical On-Resistance Vs. Gate Voltage

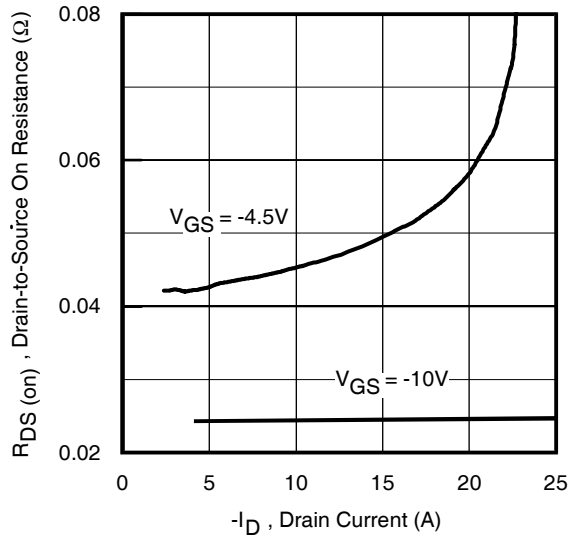


Fig 13. Typical On-Resistance Vs. Drain Current

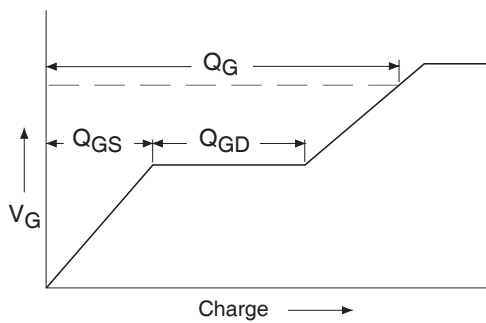


Fig 14a. Basic Gate Charge Waveform

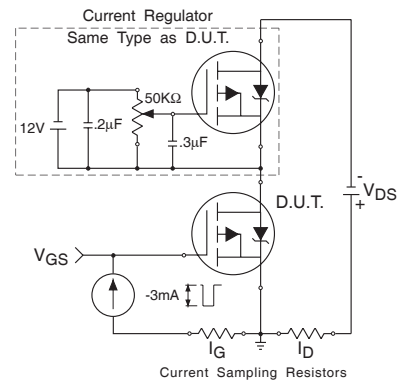


Fig 14b. Gate Charge Test Circuit

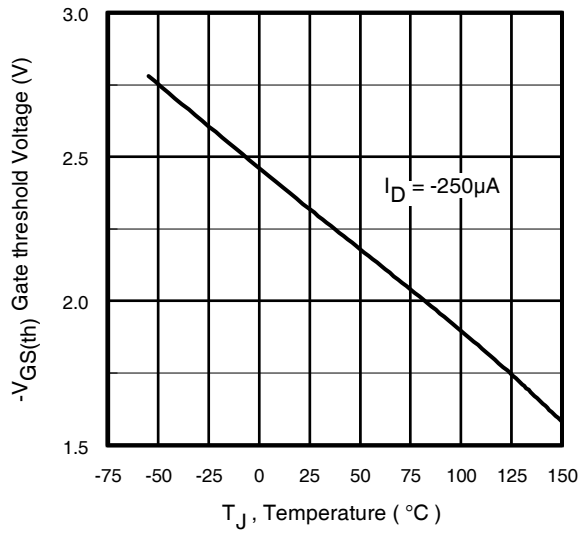


Fig 15. Typical $V_{GS(th)}$ Vs. Junction Temperature

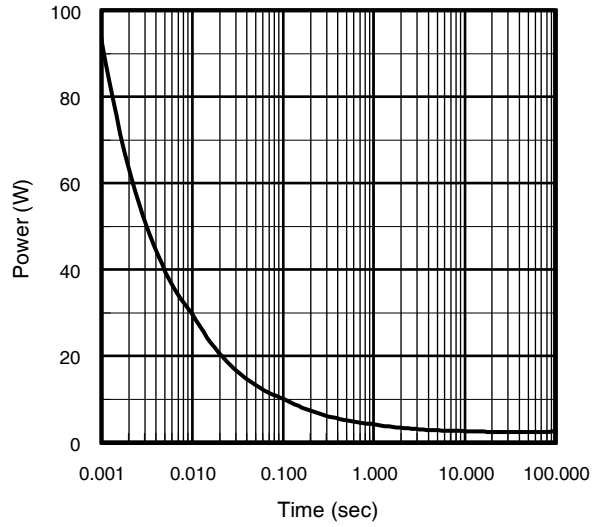


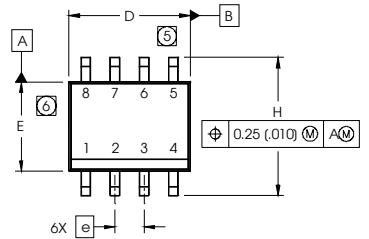
Fig 16. Typical Power Vs. Time

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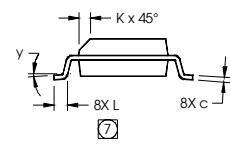
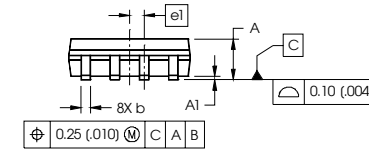


SO-8 Package Outline

Dimensions are shown in millimeters (inches)



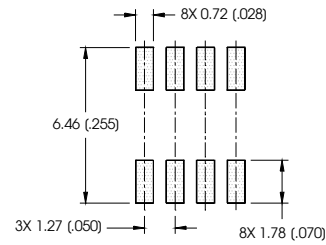
DIM	INCHES		MILLIMETERS	
	MIN	MAX	MIN	MAX
A	.0532	.0688	1.35	1.75
A1	.0040	.0098	0.10	0.25
b	.013	.020	0.33	0.51
c	.0075	.0098	0.19	0.25
D	.189	.1968	4.80	5.00
E	.1497	.1574	3.80	4.00
e	.050 BASIC		1.27 BASIC	
e1	.025 BASIC		0.635 BASIC	
H	.2284	.2440	5.80	6.20
K	.0099	.0196	0.25	0.50
L	.016	.050	0.40	1.27
y	0°	8°	0°	8°



NOTES:

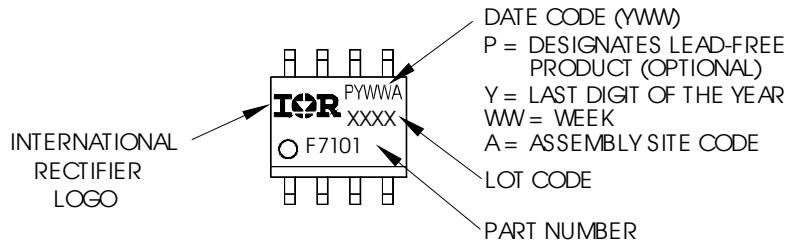
1. DIMENSIONING & TOLERANCING PER ASME Y14.5M-1994.
2. CONTROLLING DIMENSION: MILLIMETER
3. DIMENSIONS ARE SHOWN IN MILLIMETERS (INCHES).
4. OUTLINE CONFORMS TO JEDEC OUTLINE MS-012AA.
- ⑤ DIMENSION DOES NOT INCLUDE MOLD PROTRUSIONS. MOLD PROTRUSIONS NOT TO EXCEED 0.15 (.006).
- ⑥ DIMENSION DOES NOT INCLUDE MOLD PROTRUSIONS. MOLD PROTRUSIONS NOT TO EXCEED 0.25 (.010).
- ⑦ DIMENSION IS THE LENGTH OF LEAD FOR SOLDERING TO A SUBSTRATE.

FOOTPRINT



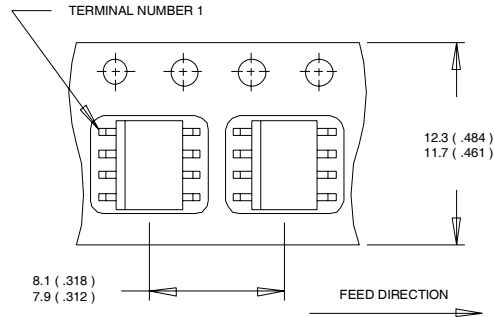
SO-8 Part Marking Information (Lead-Free)

EXAMPLE: THIS IS AN IRF7101 (MOSFET)

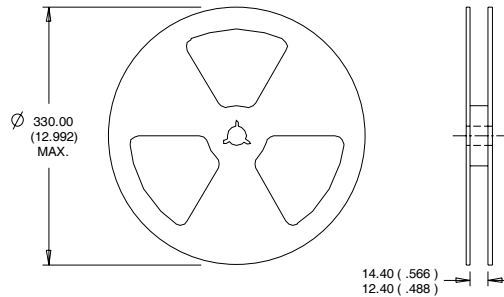


SO-8 Tape and Reel

Dimensions are shown in millimeters (inches)



- NOTES:
1. CONTROLLING DIMENSION : MILLIMETER.
 2. ALL DIMENSIONS ARE SHOWN IN MILLIMETERS(INCHES).
 3. OUTLINE CONFORMS TO EIA-481 & EIA-541.



- NOTES:
1. CONTROLLING DIMENSION : MILLIMETER.
 2. OUTLINE CONFORMS TO EIA-481 & EIA-541.

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 This product has been designed and qualified for the Consumer market.
 Qualification Standards can be found on IR's Web site.

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